

|   | Type | L # | Hits | Search Text                  | DBs   | Time Stamp           | Comments |
|---|------|-----|------|------------------------------|---|----------------------|----------|
| 1 | BRS  | L1  | 0    | wuwen adj1 yi.in.            | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:18 |          |
| 2 | BRS  | L2  | 0    | diana adj1<br>morales.in.    | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:18 |          |
| 3 | BRS  | L3  | 16   | chi adj1 wu.in.              | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:18 |          |
| 4 | BRS  | L4  | 3    | 3 and physical near<br>vapor | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:19 |          |

|   | Type | L # | Hits | Search Text                     | DBs   | Time Stamp           | Comments |
|---|------|-----|------|---------------------------------|---|----------------------|----------|
| 5 | BRS  | L5  | 0    | ritesh adjl shah.in.            | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:20 |          |
| 6 | BRS  | L6  | 0    | jeff adjl keller.in.            | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:20 |          |
| 7 | BRS  | L7  | 1856 | 438/612.ccls.                   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:20 |          |
| 8 | BRS  | L8  | 22   | 7 and (physical near1<br>vapor) | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:25 |          |

|    | Type | L # | Hits  | Search Text  | DBs   | Time Stamp           | Comments |
|----|------|-----|-------|--|---|----------------------|----------|
| 9  | BRS  | L9  | 11971 | physical near vapor<br>near deposition   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:59 |          |
| 10 | BRS  | L11 | 1     | (physical near vapor<br>near deposition)<br>near10 (non-magnetic)<br>near8 (silicon) | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:27 |          |
| 11 | BRS  | L10 | 43    | (physical near vapor<br>near deposition)<br>near10 (non-magnetic)                    | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:38 |          |
| 12 | BRS  | L12 | 177   | (PVD) near10 magnetic  | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:36 |          |

|    | Type | L # | Hits | Search Text   | DBs  | Time Stamp           | Comments |
|----|------|-----|------|---|--|----------------------|----------|
| 13 | BRS  | L13 | 1    | (PVD) near10 magnetic<br>near10 phase   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:36 |          |
| 14 | BRS  | L14 | 219  | (physical near vapor<br>near deposition)<br>near10 (magnetic)                   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:38 |          |
| 15 | BRS  | L15 | 4    | (physical near vapor<br>near deposition)<br>near10 (magnetic)<br>near10 (phase) | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:40 |          |
| 16 | BRS  | L16 | 36   | (vapor near<br>deposition) near10<br>(magnetic) near10<br>(phase)               | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:40 |          |

|    | Type | L # | Hits | Search Text  | DBs  | Time Stamp           | Comments |
|----|------|-----|------|--|--|----------------------|----------|
| 17 | BRS  | L17 | 2    | (vapor near deposition) near10<br>(magnetic) near10<br>(phase) near10<br>(silicon) | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:42 |          |
| 18 | BRS  | L18 | 264  | (vapor near deposition) near10<br>(phase) near10<br>(silicon)                      | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:42 |          |
| 19 | BRS  | L19 | 2    | (vapor near deposition) near10<br>(one near phase) near10 (silicon)                | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:44 |          |
| 20 | BRS  | L20 | 6    | (vapor near deposition) near10<br>(one near phase)                                 | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM_<br>TDB | 2003/02/1<br>1 17:50 |          |

|    | Type | L # | Hits  | Search Text   | DBs   | Time Stamp           | Comments |
|----|------|-----|-------|---|---|----------------------|----------|
| 21 | BRS  | L21 | 88901 | (film) near10<br>deposition   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:50 |          |
| 22 | BRS  | L22 | 25835 | (thin near film)<br>near10 deposition                               | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:51 |          |
| 23 | BRS  | L23 | 0     | (thin near film)<br>near10 deposition<br>near10 (one near<br>phase) | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:52 |          |
| 24 | BRS  | L24 | 1     | (thin near film)<br>near10 deposition<br>near20 (one near<br>phase) | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:53 |          |

|    | Type | L # | Hits       | Search Text  | DBs   | Time Stamp           | Comments |
|----|------|-----|------------|--|---|----------------------|----------|
| 25 | BRS  | L25 | 916        | (thin near film)<br>near10 deposition<br>near20 (phase)  | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:53 |          |
| 26 | BRS  | L26 | 433        | (thin near film)<br>near10 vapor near<br>deposition near20<br>(phase)                                  | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:54 |          |
| 27 | BRS  | L27 | 69654<br>1 | (thin near film)<br>near10 vapor near<br>deposition near20<br>(phase) near5 silicon                    | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:54 |          |
| 28 | BRS  | L29 | 0          | (magnetic) near5<br>(thin near film)<br>near10 vapor near<br>deposition near20<br>(phase) near silicon | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:55 |          |

|    | Type | L # | Hits | Search Text   | DBs   | Time Stamp           | Comments |
|----|------|-----|------|---|---|----------------------|----------|
| 29 | BRS  | L28 | 16   | (thin near film)<br>near10 vapor near<br>deposition near20<br>(phase) near silicon          | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:57 |          |
| 30 | BRS  | L30 | 81   | (film) near10 vapor<br>near deposition<br>near20 (phase) near<br>silicon                    | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:58 |          |
| 31 | BRS  | L31 | 1    | (magnetic near10<br>film) near10 vapor<br>near deposition<br>near20 (phase) near<br>silicon | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 17:59 |          |
| 32 | BRS  | L32 | 228  | physical near vapor<br>near deposition near3<br>target                                      | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 18:00 |          |



|    | Type | L # | Hits | Search Text  | DBs  | Time Stamp           | Comments |
|----|------|-----|------|--|--|----------------------|----------|
| 33 | BRS  | L33 | 10   | magnetic near8<br>physical near vapor<br>near deposition near3<br>target           | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:04 |          |
| 34 | BRS  | L35 | 0    | silicon near8<br>physical near vapor<br>near deposition near3<br>target near phase | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:04 |          |
| 35 | BRS  | L36 | 5    | phase near8 physical<br>near vapor near<br>deposition near3<br>target              | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:05 |          |
| 36 | BRS  | L34 | 25   | silicon near8<br>physical near vapor<br>near deposition near3<br>target            | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:11 |          |

|    | Type | L # | Hits | Search Text   | DBs  | Time Stamp           | Comments |
|----|------|-----|------|---|--|----------------------|----------|
| 37 | BRS  | L37 | 440  | silicon near8<br>physical near vapor<br>near deposition                 | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:11 |          |
| 38 | BRS  | L38 | 2    | silicon near8<br>physical near vapor<br>near deposition near8<br>phase  | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:12 |          |
| 39 | BRS  | L39 | 245  | physical near vapor<br>near deposition near8<br>phase                   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:12 |          |
| 40 | BRS  | L40 | 3    | magnetic near8<br>physical near vapor<br>near deposition near8<br>phase | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:14 |          |

|    | Type | L # | Hits       | Search Text  | DBs   | Time Stamp           | Comments |
|----|------|-----|------------|--|---|----------------------|----------|
| 41 | BRS  | L41 | 13450<br>4 | 438/\$.ccls.   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 18:15 |          |
| 42 | BRS  | L42 | 11980      | 41 and (physical near<br>vapor) or (PVD)                                   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 18:15 |          |
| 43 | BRS  | L43 | 11168      | 41 and target near8<br>(physical near vapor)<br>or (PVD)                   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 18:16 |          |
| 44 | BRS  | L44 | 270        | 41 and target near8<br>(physical near vapor)<br>or (PVD) near8<br>magnetic | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM<br>TDB | 2003/02/1<br>1 18:16 |          |

|    | Type | L # | Hits | Search Text    | DBs  | Time Stamp           | Comments |
|----|------|-----|------|----------------|--|----------------------|----------|
| 45 | BRS  | L45 | 158  | 44 and silicon | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:16 |          |
| 46 | BRS  | L46 | 64   | 45 and phase   | USPA<br>T;<br>US-P<br>GPUB<br>;<br>EPO;<br>JPO;<br>DERW<br>ENT;<br>IBM-<br>TDB | 2003/02/1<br>1 18:16 |          |

|    | U                                   | 1                        | Document ID             | Title  | Current OR | Pages | Issue Date |
|----|-------------------------------------|--------------------------|-------------------------|--|------------|-------|------------|
| 1  | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US<br>20030022477<br>A1 | Formation of electroplate solder on an organic circuit board for flip chip joints and board to board solder joints                     | 438/612    | 16    | 20030130   |
| 2  | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US<br>20030013290<br>A1 | Semiconductor device and method of formation   | 438/612    | 10    | 20030116   |
| 3  | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US<br>20010053567<br>A1 | Method of forming a test insert for interfacing a device containing contact bumps with a test substrate                                | 438/127    | 25    | 20011220   |
| 4  | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US<br>20010016408<br>A1 | Mask repattern process   | 438/618    | 11    | 20010823   |
| 5  | <input type="checkbox"/>            | <input type="checkbox"/> | US 6472304<br>B2        | Wire bonding to copper   | 438/612    | 12    | 20021029   |
| 6  | <input type="checkbox"/>            | <input type="checkbox"/> | US 6461954<br>B1        | Method and an apparatus for forming an under bump metallization structure  | 438/613    | 7     | 20021008   |
| 7  | <input type="checkbox"/>            | <input type="checkbox"/> | US 6451681<br>B1        | Method of forming copper interconnection utilizing aluminum capping film   | 438/601    | 11    | 20020917   |
| 8  | <input type="checkbox"/>            | <input type="checkbox"/> | US 6448171<br>B1        | Microelectronic fabrication having formed therein terminal electrode structure providing enhanced passivation and enhanced bondability | 438/614    | 9     | 20020910   |
| 9  | <input type="checkbox"/>            | <input type="checkbox"/> | US 6420254<br>B1        | Recessed bond pad  | 438/612    | 22    | 20020716   |
| 10 | <input type="checkbox"/>            | <input type="checkbox"/> | US 6395626<br>B1        | Method of forming bonding projecting electrodes  | 438/613    | 16    | 20020528   |

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|----|--------------------------|--------------------------|------------------|--|------------|-------|------------|
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 6376353<br>B1 | Aluminum and copper bimetallic bond pad scheme for copper damascene interconnects                      | 438/612    | 18    | 20020423   |
| 12 | <input type="checkbox"/> | <input type="checkbox"/> | US 6362087<br>B1 | Method for fabricating a microelectronic fabrication having formed therein a redistribution structure  | 438/597    | 9     | 20020326   |
| 13 | <input type="checkbox"/> | <input type="checkbox"/> | US 6358832<br>B1 | Method of forming barrier layers for damascene interconnects   | 438/612    | 13    | 20020319   |
| 14 | <input type="checkbox"/> | <input type="checkbox"/> | US 6300234<br>B1 | Process for forming an electrical device   | 438/612    | 10    | 20011009   |
| 15 | <input type="checkbox"/> | <input type="checkbox"/> | US 6297140<br>B1 | Method to plate C4 to copper stud  | 438/612    | 9     | 20011002   |
| 16 | <input type="checkbox"/> | <input type="checkbox"/> | US 6281041<br>B1 | Process to make a tall solder ball by placing a eutectic solder ball on top of a high lead solder ball | 438/106    | 10    | 20010828   |
| 17 | <input type="checkbox"/> | <input type="checkbox"/> | US 6245655<br>B1 | Method for planarized deposition of a material   | 438/612    | 14    | 20010612   |
| 18 | <input type="checkbox"/> | <input type="checkbox"/> | US 6228687<br>B1 | Wafer-level package and methods of fabricating   | 438/125    | 16    | 20010508   |

|    | U                        | 1                        | Document ID      | Title  | Current OR | Pages | Issue Date |
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| 19 | <input type="checkbox"/> | <input type="checkbox"/> | US 6214716<br>B1 | Semiconductor substrate-based BGA interconnection and methods of farication same   | 438/612    | 17    | 20010410   |
| 20 | <input type="checkbox"/> | <input type="checkbox"/> | US 6198170<br>B1 | Bonding pad and support structure and method for their fabrication   | 257/784    | 24    | 20010306   |
| 21 | <input type="checkbox"/> | <input type="checkbox"/> | US 6169021<br>B1 | Method of making a metallized recess in a substrate  | 438/612    | 17    | 20010102   |
| 22 | <input type="checkbox"/> | <input type="checkbox"/> | US 6110823<br>A  | Method of modifying the thickness of a plating on a member by creating a temperature gradient on the member, applications for employing such a method, and structures resulting from such a method | 438/660    | 130   | 20000829   |